



Technical Data Sheet

ACS Material Mechanically Exfoliated Single Crystal Graphene On SiO₂/Si (SiO₂: 300nm Thick)

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1. Preparation Method

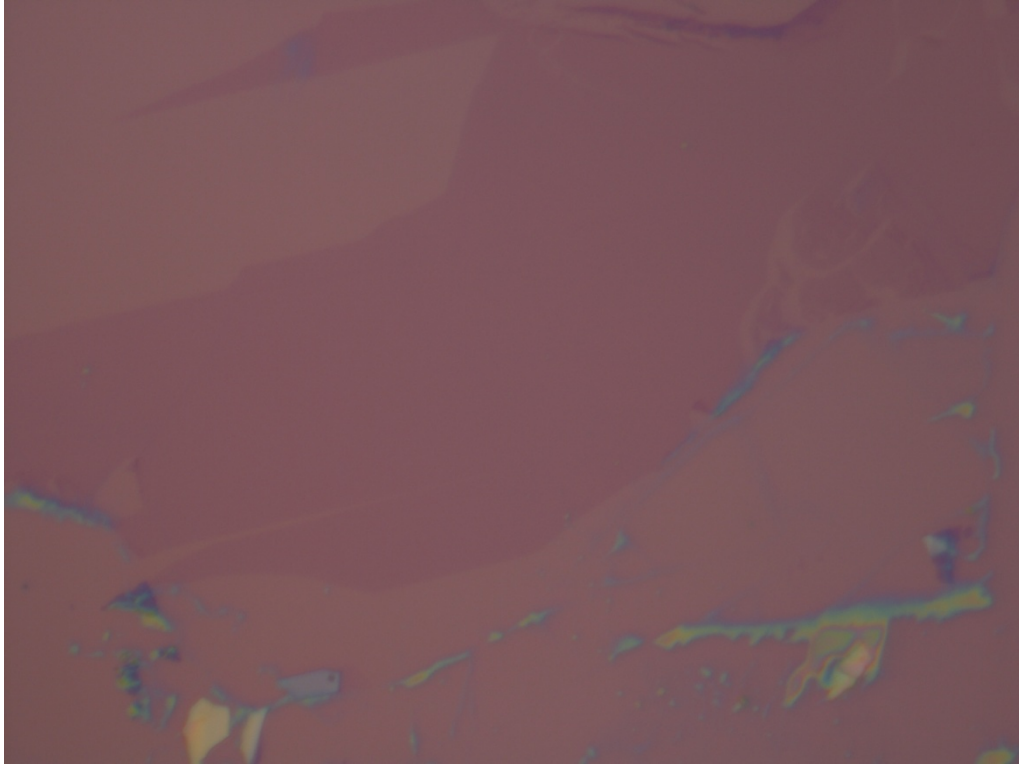
Mechanical Exfoliation method

2. Characterizations

| Graphene Layer: | Monolayer, Single Crystal | Bilayer, Single Crystal |
|---------------------------------|---|---|
| Substrate: | SiO ₂ / Si | SiO ₂ / Si |
| Substrate size: | 1 cm x 1 cm 1.5cm x 1.5cm 2cm x 2cm | 1cm x 1cm 1.5cm x 1.5cm 2cm x 2cm |
| Thickness of SiO ₂ : | 300 nm | 300 nm |
| Thickness of Si: | 500 μm | 500 μm |
| Graphene Area: | >5000 μm ² | >5000 μm ² |



Typical Image of ACS Material Mechanically Exfoliated Monolayer Graphene on 300nm SiO₂



Typical Image of ACS Material Mechanically Exfoliated Monolayer Graphene on 300nm SiO₂



Typical Image of ACS Material Mechanically Exfoliated Bilayer Graphene on 300nm SiO₂

3. Application Fields

- 1) Gas-sensitive materials
- 2) Electronic displays
- 3) Composite materials

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